

P2N2907A

Amplifier Transistor

PNP Silicon

Features

- These are Pb-Free Devices*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	-60	Vdc
Collector-Base Voltage	V_{CBO}	-60	Vdc
Emitter-Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current - Continuous	I_C	-600	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625 5.0	mW mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5 12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

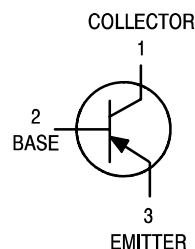
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	83.3	$^\circ\text{C/W}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

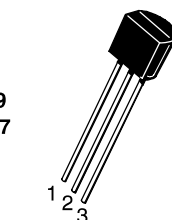


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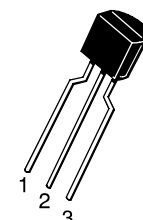
<http://onsemi.com>



TO-92
CASE 29
STYLE 17

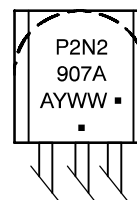


STRAIGHT LEAD
BULK PACK



BENT LEAD
TAPE & REEL
AMMO PACK

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
P2N2907AG	TO-92 (Pb-Free)	5000 Units / Bulk
P2N2907ARL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Breakdown Voltage (Note 1) (I _C = -10 mA _{dc} , I _B = 0)	V _{(BR)CEO}	-60	-	V _{dc}
Collector-Base Breakdown Voltage (I _C = -10 μA _{dc} , I _E = 0)	V _{(BR)CBO}	-60	-	V _{dc}
Emitter-Base Breakdown Voltage (I _E = -10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	-5.0	-	V _{dc}
Collector Cutoff Current (V _{CE} = -30 V _{dc} , V _{EB(off)} = -0.5 V _{dc})	I _{CEX}	-	-50	nA _{dc}
Collector Cutoff Current (V _{CB} = -50 V _{dc} , I _E = 0) (V _{CB} = -50 V _{dc} , I _E = 0, T _A = 150°C)	I _{CBO}	-	-0.01 -10	μA _{dc}
Emitter Cutoff Current (V _{EB} = -3.0 V _{dc})	I _{EBO}	-	-10	nA _{dc}
Collector Cutoff Current (V _{CE} = -10 V)	I _{CEO}	-	-10	nA _{dc}
Base Cutoff Current (V _{CE} = -30 V _{dc} , V _{EB(off)} = -0.5 V _{dc})	I _{BEX}	-	-50	nA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = -0.1 mA _{dc} , V _{CE} = -10 V _{dc}) (I _C = -1.0 mA _{dc} , V _{CE} = -10 V _{dc}) (I _C = -10 mA _{dc} , V _{CE} = -10 V _{dc}) (I _C = -150 mA _{dc} , V _{CE} = -10 V _{dc}) (Note 1) (I _C = -500 mA _{dc} , V _{CE} = -10 V _{dc}) (Note 1)	h _{FE}	75 100 100 100 50	- - - 300 -	-
Collector-Emitter Saturation Voltage (Note 1) (I _C = -150 mA _{dc} , I _B = -15 mA _{dc}) (I _C = -500 mA _{dc} , I _B = -50 mA _{dc})	V _{CE(sat)}	- -	-0.4 -1.6	V _{dc}
Base-Emitter Saturation Voltage (Note 1) (I _C = -150 mA _{dc} , I _B = -15 mA _{dc}) (I _C = -500 mA _{dc} , I _B = -50 mA _{dc})	V _{BE(sat)}	- -	-1.3 -2.6	V _{dc}

SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product (Notes 1 and 2) (I _C = -50 mA _{dc} , V _{CE} = -20 V _{dc} , f = 100 MHz)	f _T	200	-	MHz
Output Capacitance (V _{CB} = -10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	-	8.0	pF
Input Capacitance (V _{EB} = -2.0 V _{dc} , I _C = 0, f = 1.0 MHz)	C _{ibo}	-	30	pF

SWITCHING CHARACTERISTICS

Turn-On Time	(V _{CC} = -30 V _{dc} , I _C = -150 mA _{dc} , I _{B1} = -15 mA _{dc}) (Figures 1 and 5)	t _{on}	-	50	ns
Delay Time		t _d	-	10	ns
Rise Time		t _r	-	40	ns
Turn-Off Time	(V _{CC} = -6.0 V _{dc} , I _C = -150 mA _{dc} , I _{B1} = I _{B2} = -15 mA _{dc}) (Figure 2)	t _{off}	-	110	ns
Storage Time		t _s	-	80	ns
Fall Time		t _f	-	30	ns

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
2. f_T is defined as the frequency at which |h_{fe}| extrapolates to unity.

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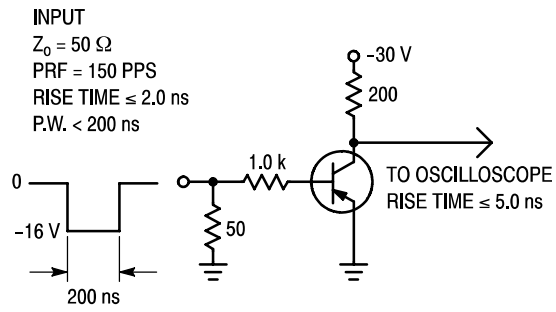


Figure 1. Delay and Rise Time Test Circuit

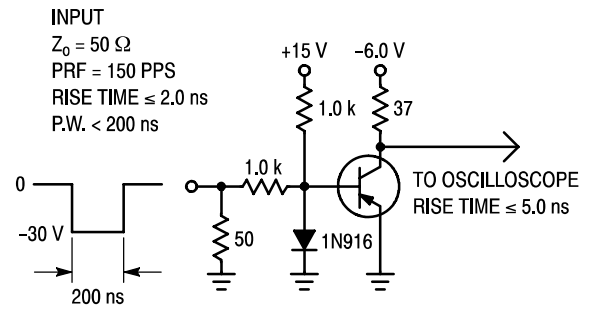


Figure 2. Storage and Fall Time Test Circuit

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TYPICAL CHARACTERISTICS

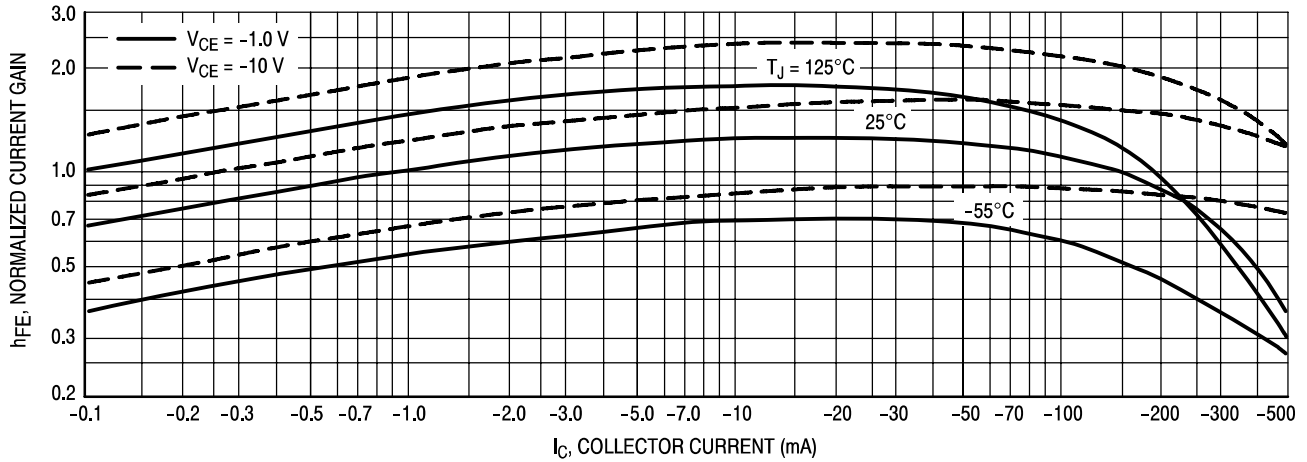


Figure 3. DC Current Gain

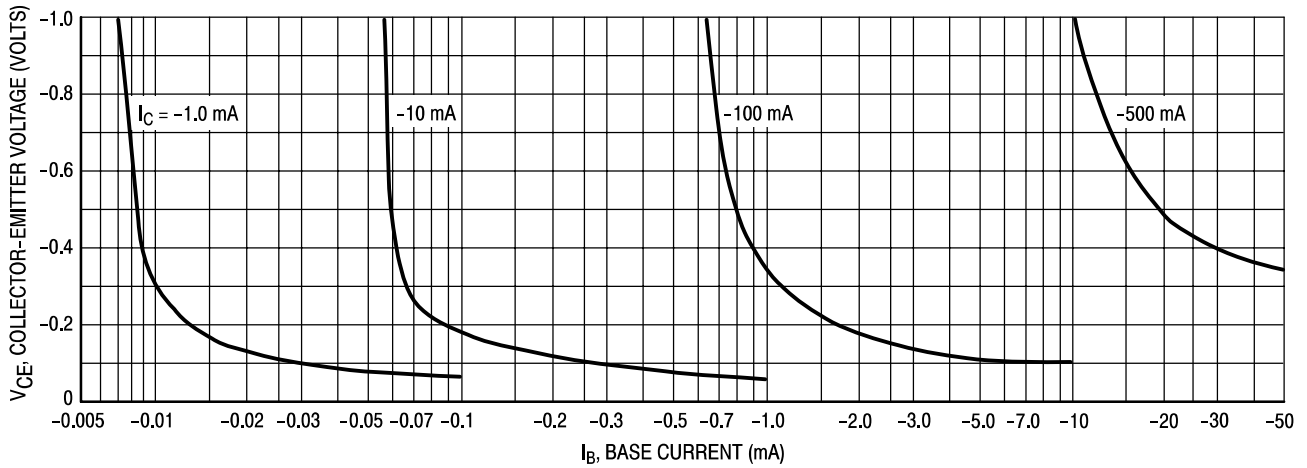


Figure 4. Collector Saturation Region

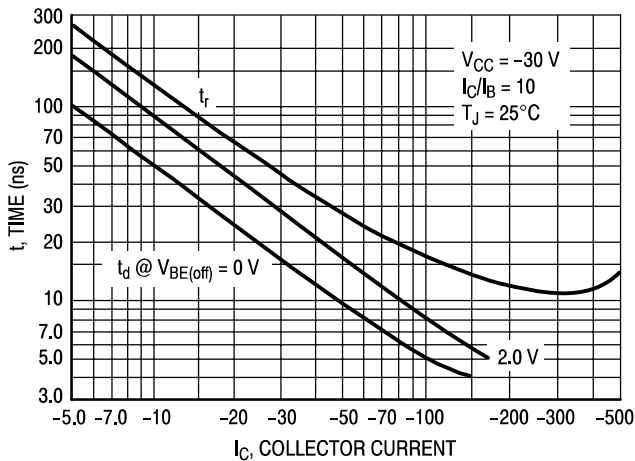


Figure 5. Turn-On Time

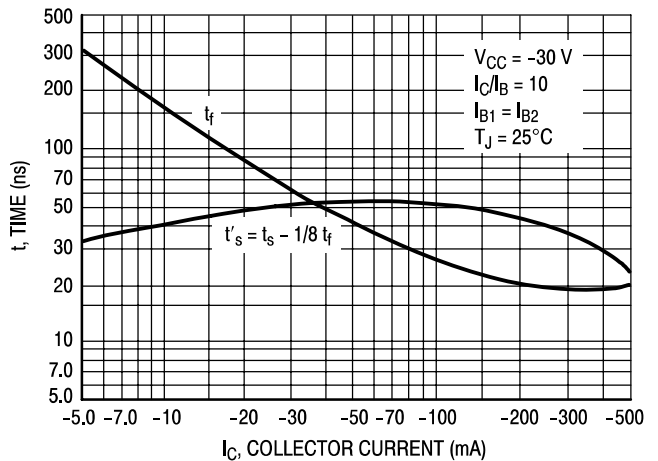


Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = 10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

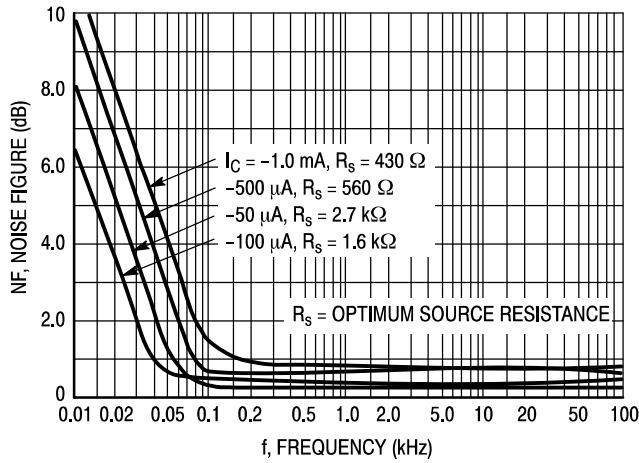


Figure 7. Frequency Effects

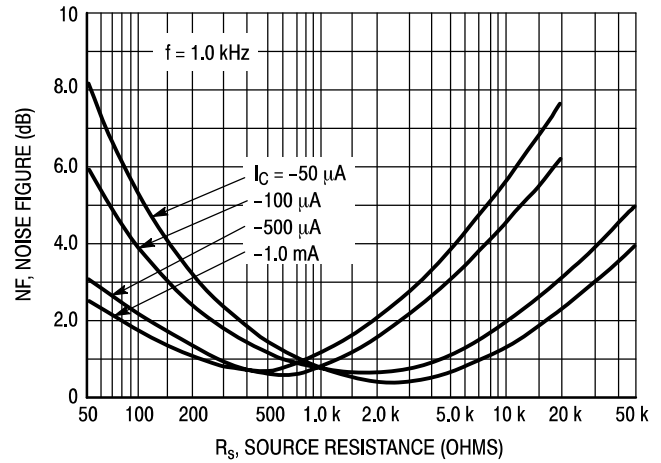


Figure 8. Source Resistance Effects

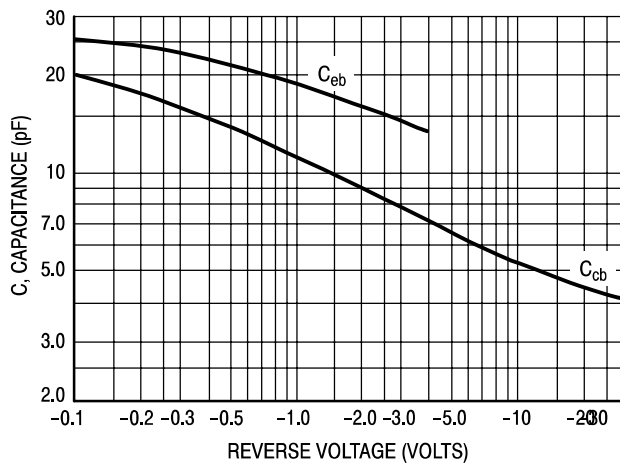


Figure 9. Capacitances

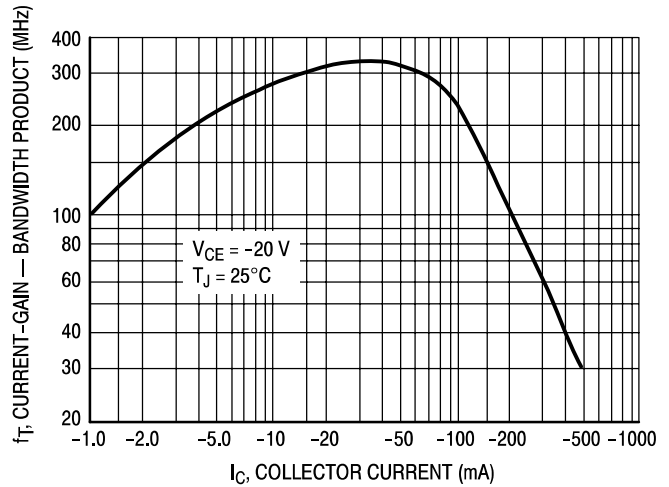


Figure 10. Current-Gain - Bandwidth Product

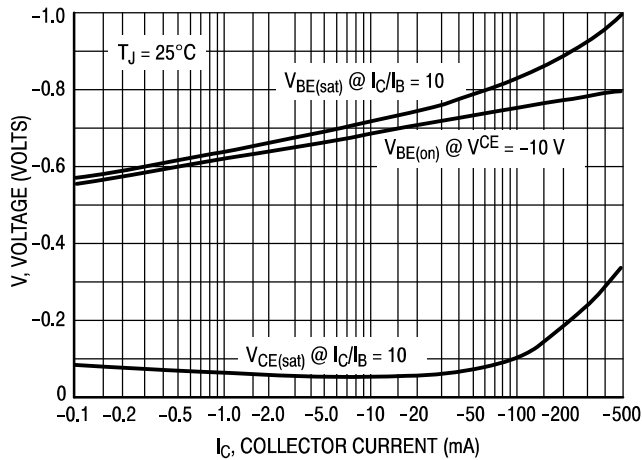


Figure 11. "On" Voltage

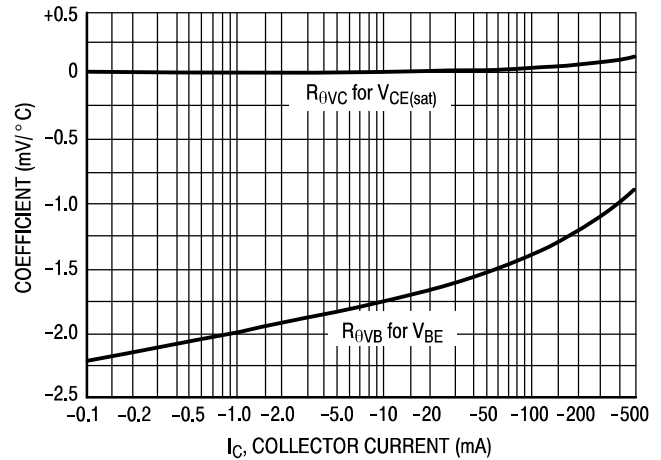
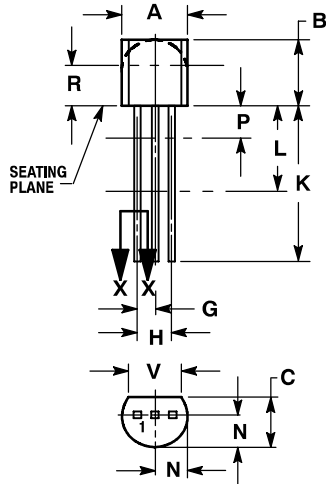


Figure 12. Temperature Coefficients

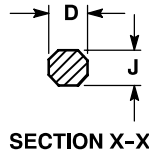
P2N2907A

PACKAGE DIMENSIONS

TO-92 (TO-226)
CASE 29-11
ISSUE AM



STRAIGHT LEAD
BULK PACK

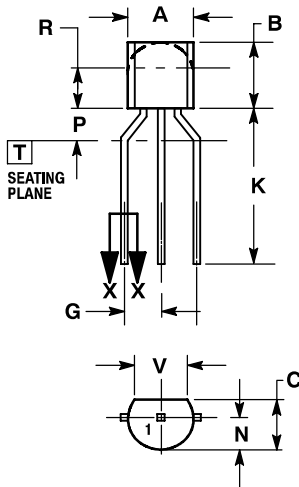


SECTION X-X

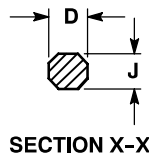
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
B	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.115	---	2.93	---
V	0.135	---	3.43	---



BENT LEAD
TAPE & REEL
AMMO PACK



SECTION X-X

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

DIM	MILLIMETERS	
	MIN	MAX
A	4.45	5.20
B	4.32	5.33
C	3.18	4.19
D	0.40	0.54
G	2.40	2.80
J	0.39	0.50
K	12.70	---
N	2.04	2.66
P	1.50	4.00
R	2.93	---
V	3.43	---

STYLE 17:

1. COLLECTOR
2. BASE
3. EMITTER

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